

DESCRIPTION

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

FEATURES

40V, 5A, $R_{DS(ON)} = 33m\Omega$ @ $V_{GS} = 10V$

Improved dv/dt capability

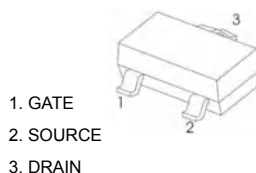
Fast switching

Green Device Available

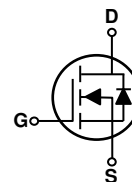
V_{DS} 40 V
 I_D 5 A
 $R_{DS(ON)}$ 33 m Ω

C8TZJ

SOT-23



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_C=25^\circ\text{C}$)	5	A
	Drain Current – Continuous ($T_C=100^\circ\text{C}$)	3	A
I_{DM}	Drain Current – Pulsed ¹	20	A
P_D	Power Dissipation ($T_C=25^\circ\text{C}$)	1.56	W
	Power Dissipation – Derate above 25°C	0.012	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise specified)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	40	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.04	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =40V, V _{GS} =0V, T _J =25°C	---	---	1	μA
		V _{DS} =32V, V _{GS} =0V, T _J =125°C	---	---	10	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance ³	V _{GS} =10V, I _D =2A	---	33	42	mΩ
		V _{GS} =4.5V, I _D =1.5A	---	45	70	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250μA	1.0	1.6	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =4A	---	6	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{2, 3}	V _{DS} =20V, V _{GS} =4.5V, I _D =3A		4.7		nC
Q _{gs}	Gate-Source Charge ^{2, 3}			0.45		
Q _{gd}	Gate-Drain Charge ^{2, 3}			1.65		
T _{d(on)}	Turn-On Delay Time ^{2, 3}	V _{DD} =20V, V _{GS} =4.5V, R _G =25Ω I _D =1A		3.2		ns
T _r	Rise Time ^{2, 3}			8.6		
T _{d(off)}	Turn-Off Delay Time ^{2, 3}			18		
T _f	Fall Time ^{2, 3}			6		
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz		420		pF
C _{oss}	Output Capacitance			65		
C _{rss}	Reverse Transfer Capacitance			40		

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	5	A
I _{SM}	Pulsed Source Current ³		---	---	10	A
V _{SD}	Diode Forward Voltage ³	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =1A, di/dt=100A/μs	---	20	---	ns
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	7.5	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

RATING AND CHARACTERISTIC CURVES

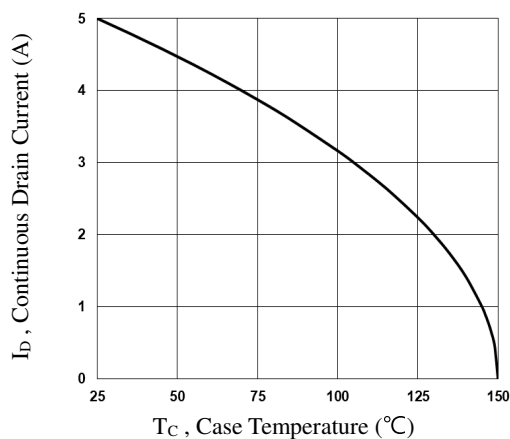


Fig.1 Continuous Drain Current vs. T_C

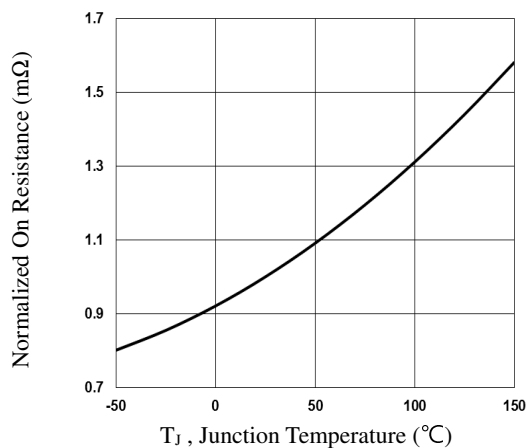


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

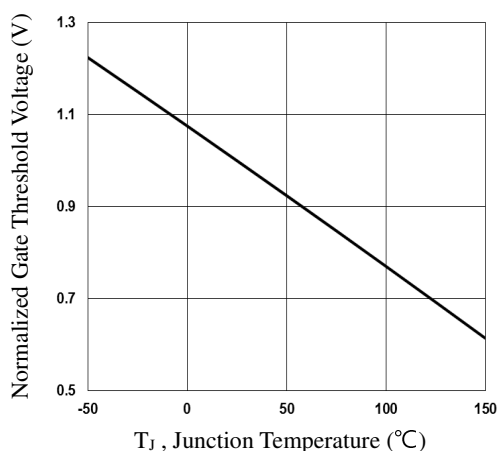


Fig.3 Normalized V_{th} vs. T_J

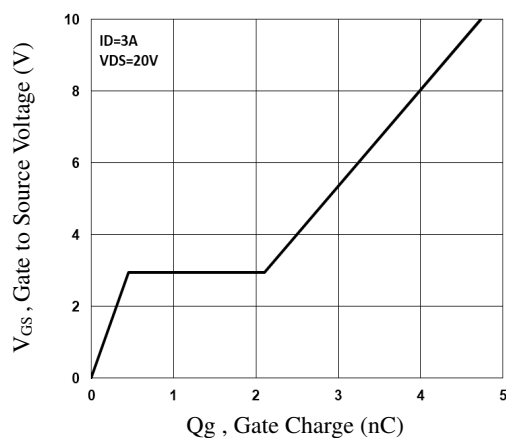


Fig.4 Gate Charge Waveform

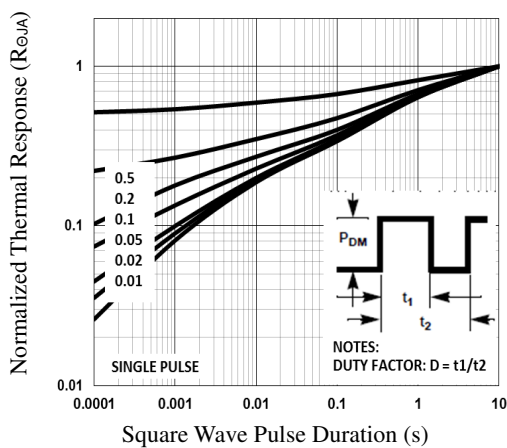


Fig.5 Normalized Transient Response

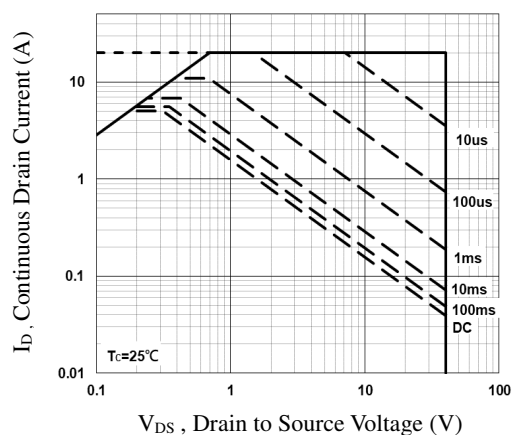
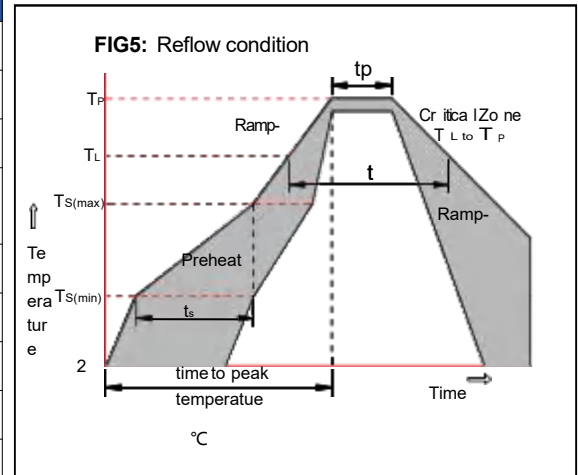


Fig.6 Maximum Safe Operation Area

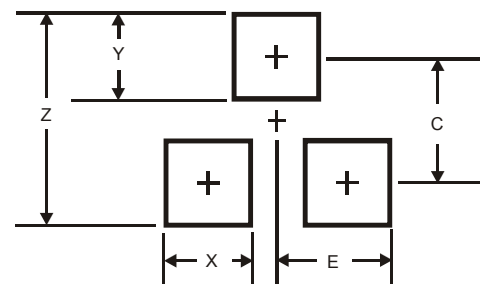
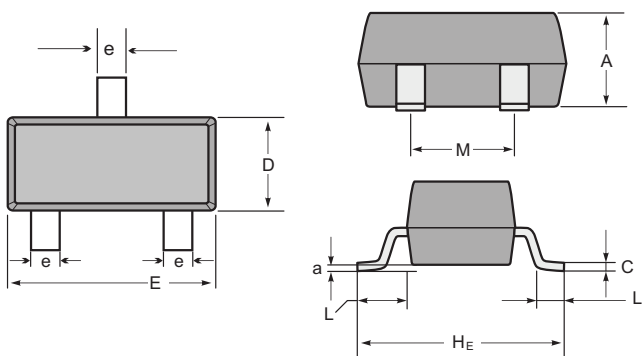
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



Package Dimensions & Suggested Pad Layout

SOT23

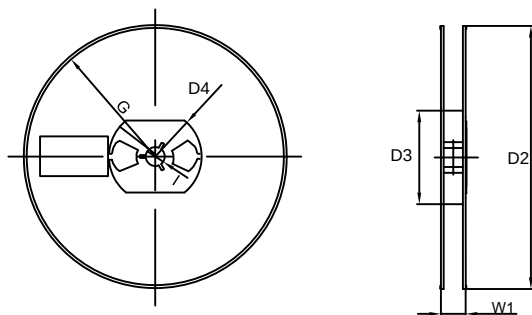


SOT-23 mechanical data

UNIT		A	C	D	E	H _E	e	M	L	L ₁	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Dimensions	SOT23
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Tape



Symbol	Dimension (mm)
P0	4.00±0.10
P1	4.00±0.10
P2	2.00±0.10
D0	1.55±0.10
D1	1.05±0.10
E	1.55±0.10
F	3.60±0.10
W	8.00±0.10
A0	3.80±0.20
B0	3.25±0.20
K0	1.45±0.10
T	0.25±0.05
D2	178.0±3.0
D3	55Min.
D4	R24.0±3.0
G	R82.0±3.0
I	13.0±2.0
W1	11.0±3.0

Quantity: 3000PCS